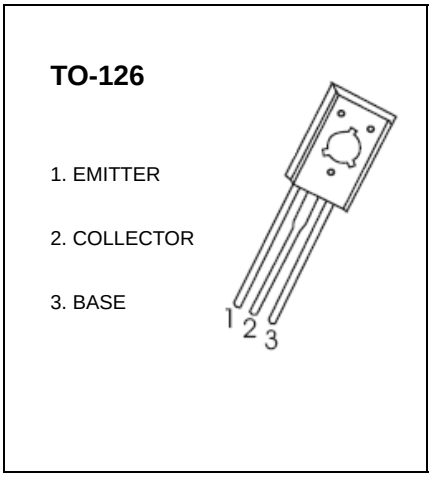
ShenzhenTaimaoTechnology Co.,Ltd.

TO-126 Plastic-Encapsulate Transistors

2SB776 TRANSISTOR (PNP)



FEATURES

- High Current Output Up to 3A
- Low Saturation Voltage Power Dissipation

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-3	A
P_C	Collector Power Dissipation	1	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-5mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V,I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V,I_C=-20mA	100			
	$h_{FE(2)}$	V_{CE}=-2V,I_C=-1A	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A,I_B=-200mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-2A,I_B=-200mA			-2	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-100mA		80		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		45		pF